

# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	3.0 2.5	А
Pulsed Drain Current (10µs pulse, Duty cycle = 1%)			I <sub>DM</sub>	10	А

# **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Power Dissipation	(Note 5)	Б	0.6	W	
Total Power Dissipation	(Note 6)	$P_D$	1.8	W	
Thermal Desigtance, Junction to Ambient	(Note 5)	Б	200	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	67		
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

## Electrical Characteristics N-CHANNEL (@TA = +25°C, unless otherwise specified.)

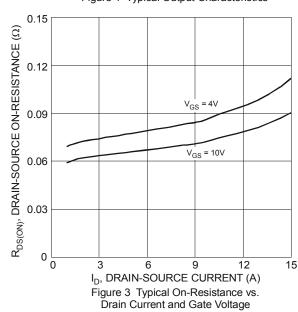
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	-	-	٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	1	1	1.0	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	_	3	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D		67	85	mΩ	$V_{GS} = 10V, I_D = 1.5A$	
Static Dialii-Source Off-Resistance	R <sub>DS (ON)</sub>		74	120	11122	$V_{GS} = 4V, I_D = 0.5A$	
Forward Transfer Admittance	Y <sub>fs</sub>	1	2.6	1	S	$V_{DS} = 5V, I_D = 1.5A$	
Diode Forward Voltage	$V_{SD}$	1	0.7	1.2	٧	$V_{GS} = 0V$ , $I_S = 3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		606	_	pF	-V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, -f = 1.0MHz	
Output Capacitance	Coss	_	32.6	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	24.6	_	pF	1 - 1.0Wi12	
Gate Resistance	$R_g$	_	1.5	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> =10V)	Qg	_	12.3	_	nC	-V <sub>DS</sub> = 30V, I <sub>D</sub> = 3A	
Total Gate Charge (V <sub>GS</sub> =4.5V)	Qg	_	5.6	_	nC		
Gate-Source Charge	Qgs	_	1.7	_	nC		
Gate-Drain Charge	Q <sub>gd</sub>	_	1.9	_	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	3.5	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_{G} = 20\Omega, R_{L} = 50\Omega$	
Turn-On Rise Time	t <sub>r</sub>		4.1		ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	35	_	ns		
Turn-Off Fall Time	t <sub>f</sub>	_	11	_	ns		

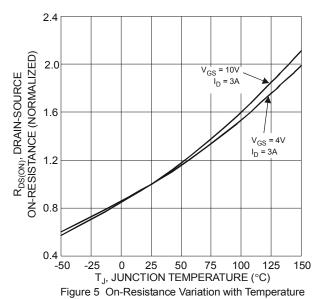
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout

Device mounted on FR-4 substrate PC board, 20z copper, with thermal vias to bottom layer 1inch square copper plate
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

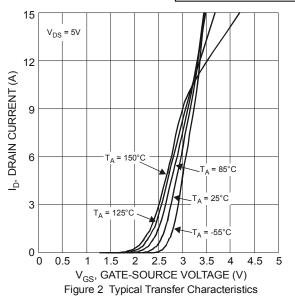


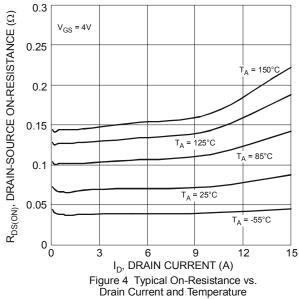
### $V_{GS} = 5V_{S}$ 12.0 = 4V ID, DRAIN CURRENT (A) 9.0 = 3.5V $V_{GS} = 3.0V$ 6.0 3.0 V<sub>GS</sub> = 2.5V 0.0 0 2 3 5 $V_{DS}$ , DRAIN-SOURCE VOLTAGE (V) Figure 1 Typical Output Characteristics

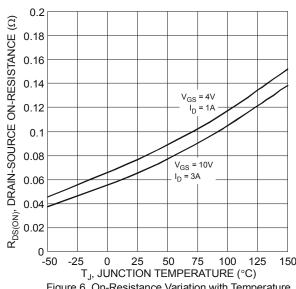




## DMN6070SFCL









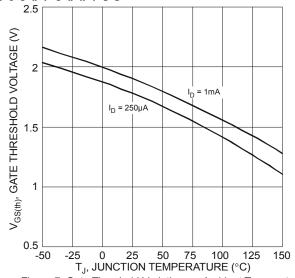


Figure 7 Gate Threshold Variation vs. Ambient Temperature

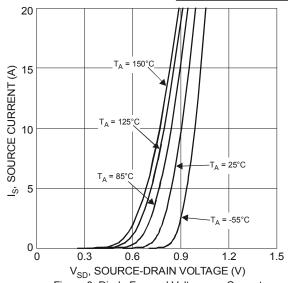
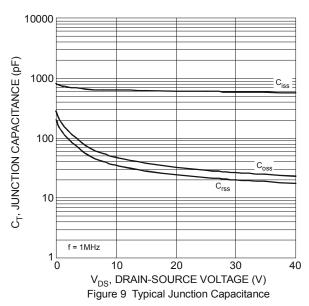
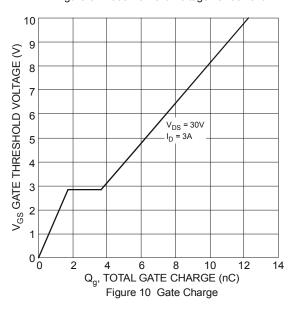


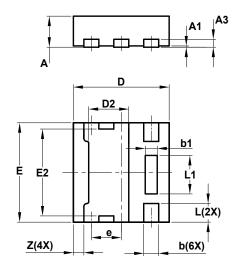
Figure 8 Diode Forward Voltage vs. Current





## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

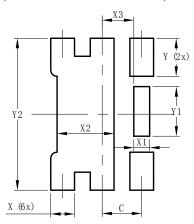


X1-DFN1616-6 Type E					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0	0.05	0.02		
А3	_	_	0.13		
b	0.20	0.30	0.25		
b1	0.10	0.30	0.20		
D	1.55	1.65	1.60		
D2	0.57	0.77	0.67		
Е	1.55	1.65	1.60		
E2	1.30	1.50	1.40		
е	_	_	0.50		
L	0.25	0.35	0.30		
L1	0.52	0.72	0.62		
Z		_	0.175		
All Dimensions in mm					



#### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)		
С	0.500		
Х	0.300		
X1	0.200		
X2	0.720		
Х3	0.400		
Υ	0.475		
Y1	0.620		
Y2	1.900		

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